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# BT234-600E

4Q Triac

23 September 2013

Product data sheet

## 1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

## 2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Triggering in all four quadrants

## 3. Applications

- General purpose motor control
- General purpose switching

## 4. Quick reference data

Table 1. Quick reference data

| Symbol                        | Parameter                            | Conditions   | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|--|-----|-----|-----|------|
| $V_{DRM}$                     | repetitive peak off-state voltage    |  | -   | -   | 600 | V    |
| $I_{TSM}$                     | non-repetitive peak on-state current | full sine wave; $T_{J(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>  | -   | -   | 35  | A    |
| $I_{T(RMS)}$                  | RMS on-state current                 | full sine wave; $T_{mb} \leq 110\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | -   | 4   | A    |
| <b>Static characteristics</b> |                                      |  |     |     |     |      |
| $I_{GT}$                      | gate trigger current                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                     | -   | -   | 10  | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                     | -   | -   | 10  | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                     | -   | -   | 10  | mA   |



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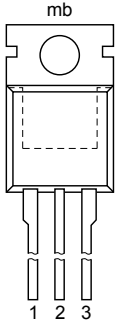
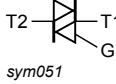
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| Symbol | Parameter | Conditions  | Min | Typ | Max | Unit |
|--------|-----------|---|-----|-----|-----|------|
|        |           | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | -   | -   | 25  | mA   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                    | Simplified outline   | Graphic symbol  |
|-----|--------|--------------------------------|--|---|
| 1   | T1     | main terminal 1                |  <p>TO-220AB (SOT78)</p> |  <p>sym051</p> |
| 2   | T2     | main terminal 2                |  |   |
| 3   | G      | gate                           |  |   |
| mb  | T2     | mounting base; main terminal 2 |  |   |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package  |  |         |
|-------------|----------|--|---------|
|             | Name     | Description  | Version |
| BT234-600E  | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |

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## 7. Limiting values

**Table 4. Limiting values**

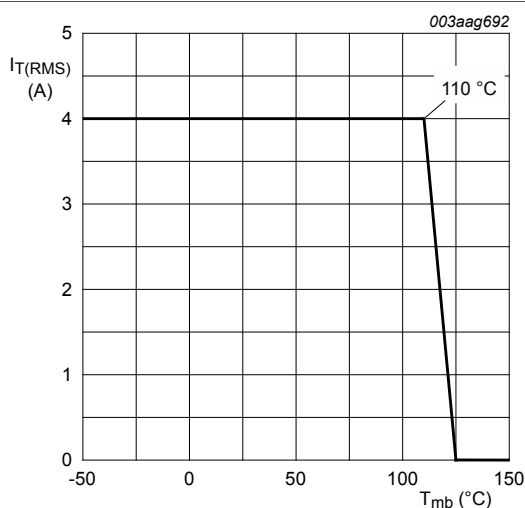
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                            | Conditions  | Min | Max  | Unit                   |
|---------------------|--------------------------------------|---|-----|------|------------------------|
| $V_{\text{DRM}}$    | repetitive peak off-state voltage    |   | -   | 600  | V                      |
| $I_{\text{T(RMS)}}$ | RMS on-state current                 | full sine wave; $T_{\text{mb}} \leq 110\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>         | -   | 4    | A                      |
| $I_{\text{TSM}}$    | non-repetitive peak on-state current | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | 35   | A                      |
|                     |                                      | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 16.7\text{ ms}$   | -   | 38.5 | A                      |
| $I^2t$              | $I^2t$ for fusing                    | $t_{\text{p}} = 10\text{ ms}$ ; SIN   | -   | 6.1  | $\text{A}^2\text{s}$   |
| $di_{\text{T}}/dt$  | rate of rise of on-state current     | $I_{\text{T}} = 7\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2+ G+                                | -   | 50   | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 7\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2+ G-                                | -   | 50   | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 7\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2- G-                                | -   | 50   | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 7\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2- G+                                | -   | 10   | $\text{A}/\mu\text{s}$ |
| $I_{\text{GM}}$     | peak gate current                    |   | -   | 2    | A                      |
| $P_{\text{GM}}$     | peak gate power                      |   | -   | 5    | W                      |
| $P_{\text{G(AV)}}$  | average gate power                   | over any 20 ms period   | -   | 0.5  | W                      |
| $T_{\text{stg}}$    | storage temperature                  |   | -40 | 150  | $^{\circ}\text{C}$     |
| $T_{\text{j}}$      | junction temperature                 |   | -   | 125  | $^{\circ}\text{C}$     |

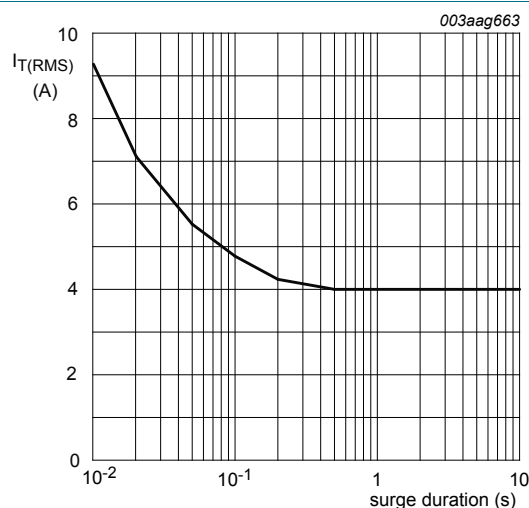
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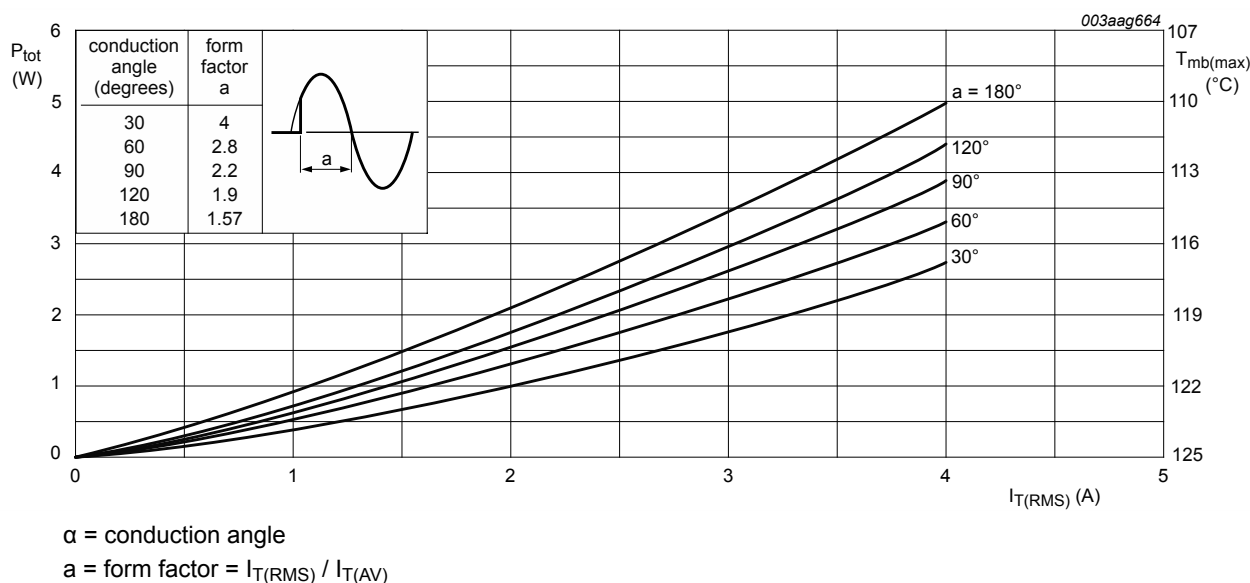


**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**



$f = 50 \text{ Hz}$ ;  $T_{mb} = 110^\circ\text{C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

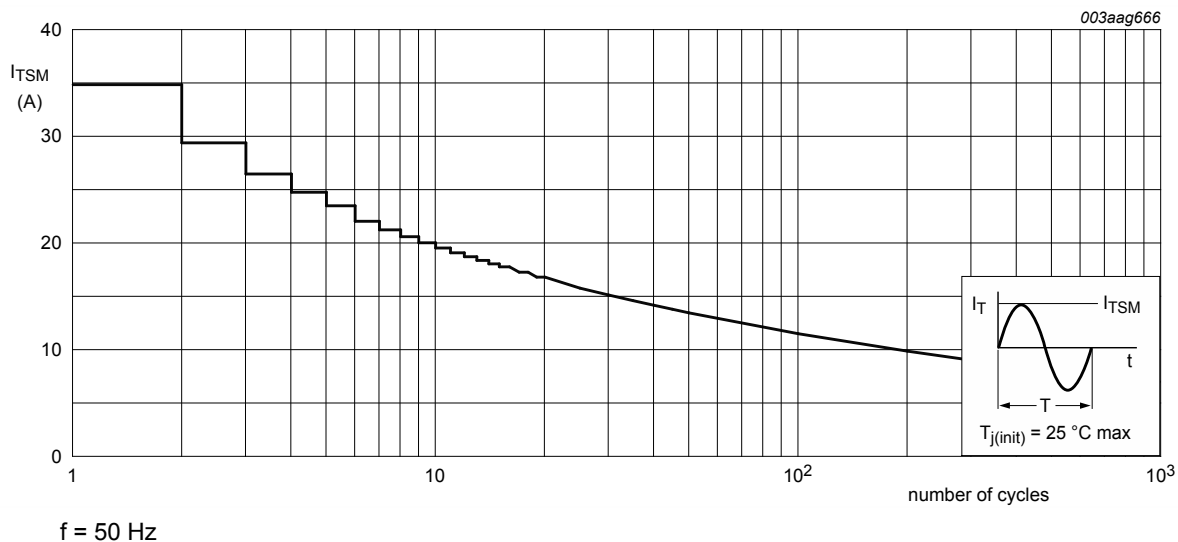


**Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values**

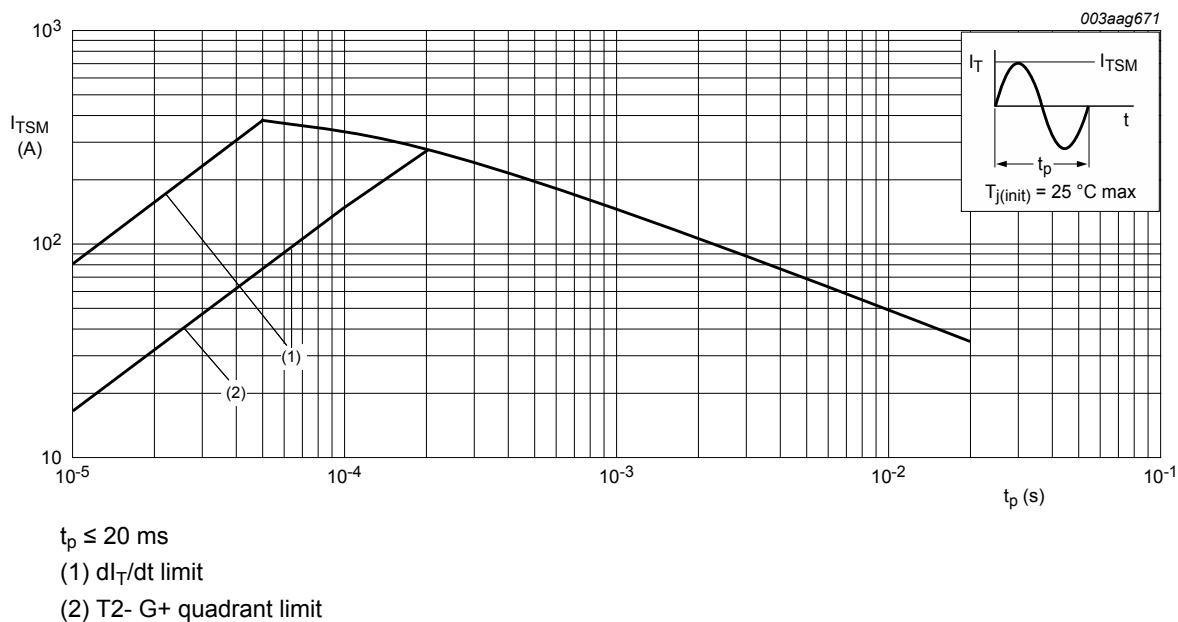
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**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**



**Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values**

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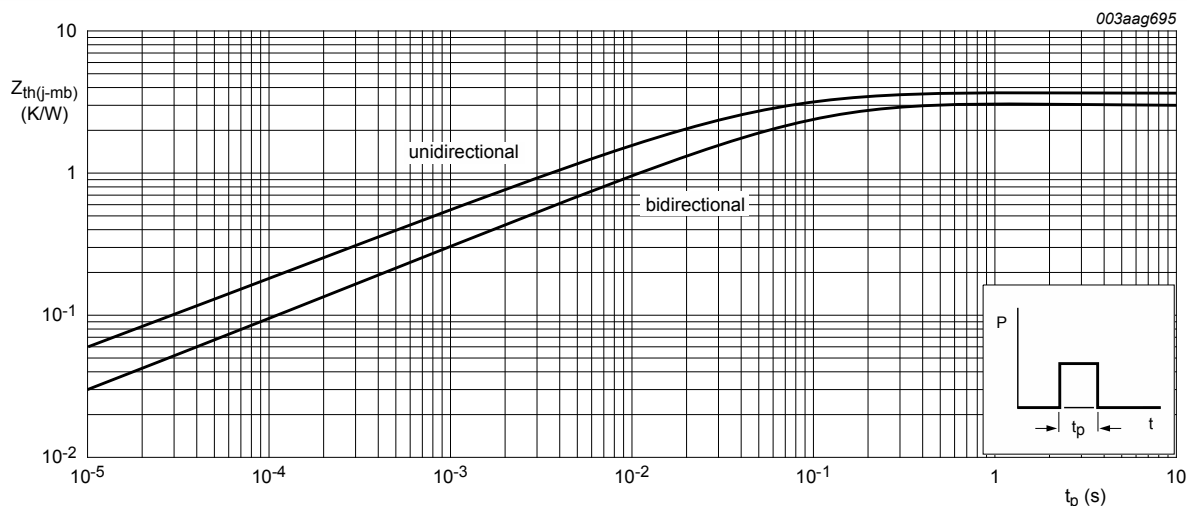
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### 8. Thermal characteristics

**Table 5. Thermal characteristics**

| Symbol         | Parameter   | Conditions                         | Min | Typ | Max | Unit |
|----------------|---|------------------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | half cycle; <a href="#">Fig. 6</a> | -   | -   | 3.7 | K/W  |
|                |   | full cycle; <a href="#">Fig. 6</a> | -   | -   | 3   | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | in free air                        | -   | 60  | -   | K/W  |



**Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration**

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### 9. Characteristics

Table 6. Characteristics

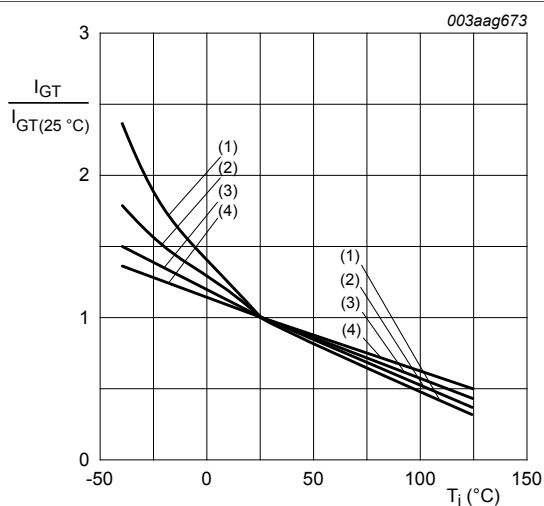
| Symbol                         | Parameter                             | Conditions  | Min  | Typ | Max | Unit             |
|--------------------------------|---------------------------------------|---|------|-----|-----|------------------|
| <b>Static characteristics</b>  |                                       |   |      |     |     |                  |
| $I_{GT}$                       | gate trigger current                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>   | -    | -   | 10  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>   | -    | -   | 10  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>   | -    | -   | 10  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>   | -    | -   | 25  | mA               |
| $I_L$                          | latching current                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>   | -    | -   | 15  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>   | -    | -   | 25  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>   | -    | -   | 15  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>   | -    | -   | 15  | mA               |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>   | -    | -   | 15  | mA               |
| $V_T$                          | on-state voltage                      | $I_T = 6\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>   | -    | 1.3 | 1.5 | V                |
| $V_{GT}$                       | gate trigger voltage                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>  | -    | 0.7 | 1   | V                |
|                                |                                       | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>  | 0.25 | 0.4 | -   | V                |
| $I_D$                          | off-state current                     | $V_D = 600\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$  | -    | 0.1 | 0.5 | mA               |
| <b>Dynamic characteristics</b> |                                       |   |      |     |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit                                     | 80   | -   | -   | V/ $\mu\text{s}$ |
| $dV_{com}/dt$                  | rate of change of commutating voltage | $V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $dI_{com}/dt = 1.8\text{ A/ms}$ ; $I_T = 4\text{ A}$ ; gate open circuit   | 15   | -   | -   | V/ $\mu\text{s}$ |
| $dI_{com}/dt$                  | rate of change of commutating current | $V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 4\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit | 1.5  | -   | -   | A/ms             |
| $t_{gt}$                       | gate-controlled turn-on time          | $I_{TM} = 6\text{ A}$ ; $V_D = 400\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$  | -    | 2   | -   | $\mu\text{s}$    |



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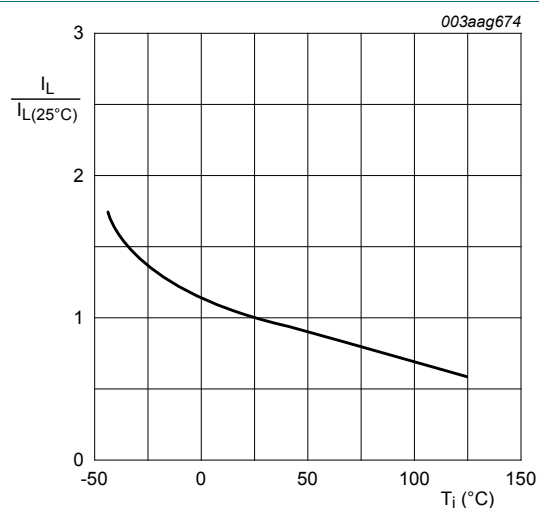
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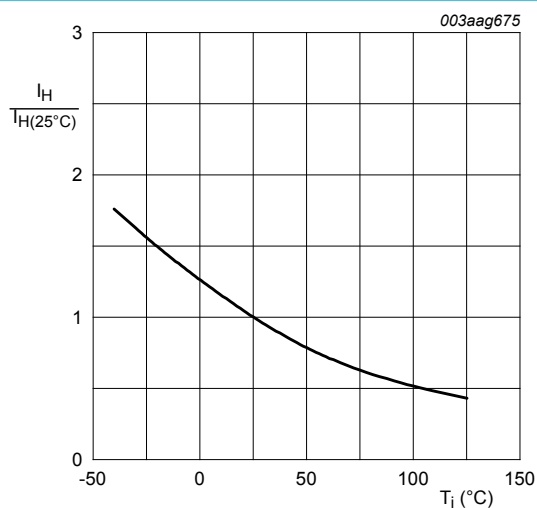


- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

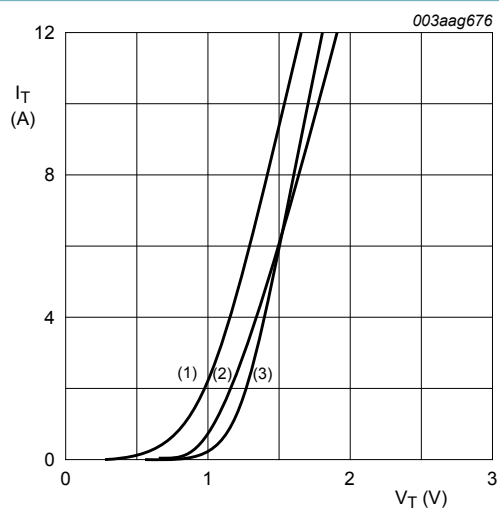
**Fig. 7. Normalized gate trigger current as a function of junction temperature**



**Fig. 8. Normalized latching current as a function of junction temperature**



**Fig. 9. Normalized holding current as a function of junction temperature**



$V_o = 1.035 \text{ V}$ ;  $R_s = 0.078 \Omega$

(1)  $T_j = 125^\circ\text{C}$ ; typical values

(2)  $T_j = 125^\circ\text{C}$ ; maximum values

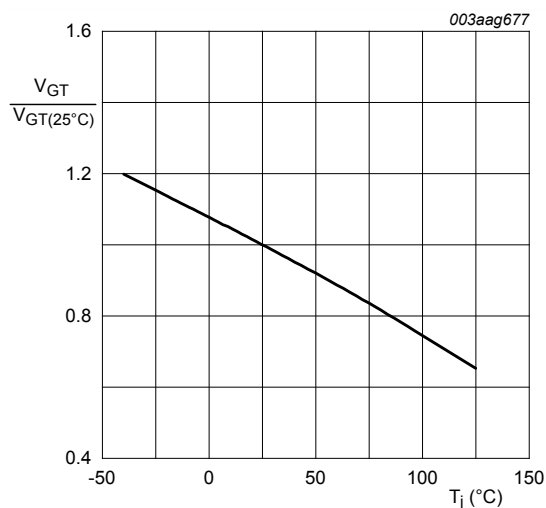
(3)  $T_j = 25^\circ\text{C}$ ; maximum values

**Fig. 10. On-state current as a function of on-state voltage**

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**Fig. 11. Normalized gate trigger voltage as a function of junction temperature**

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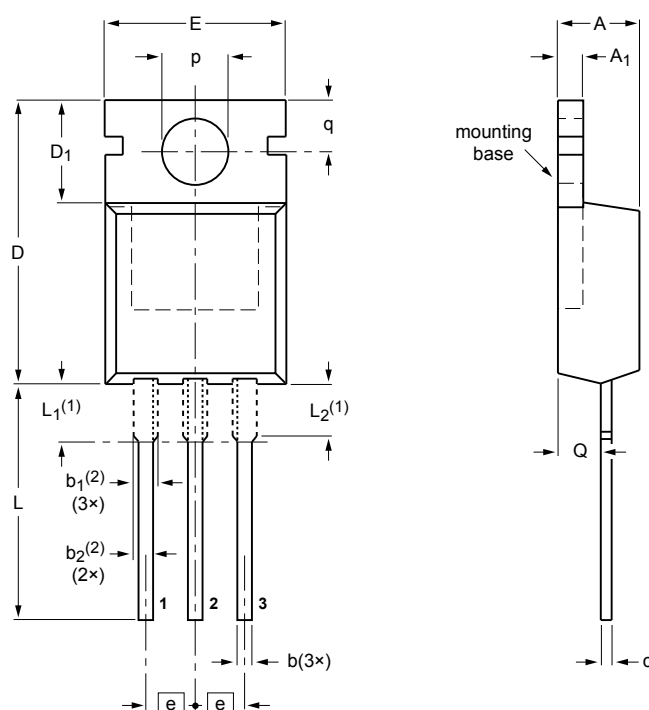
## BT234-600E

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### 10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



0 5 10 mm  
scale

**DIMENSIONS** (mm are the original dimensions)

| UNIT | A          | A <sub>1</sub> | b          | b <sub>1</sub> (2) | b <sub>2</sub> (2) | c          | D            | D <sub>1</sub> | E           | e    | L            | L <sub>1</sub> (1) | L <sub>2</sub> (1)<br>max. | p          | q          | Q          |
|------|------------|----------------|------------|--------------------|--------------------|------------|--------------|----------------|-------------|------|--------------|--------------------|----------------------------|------------|------------|------------|
| mm   | 4.7<br>4.1 | 1.40<br>1.25   | 0.9<br>0.6 | 1.6<br>1.0         | 1.3<br>1.0         | 0.7<br>0.4 | 16.0<br>15.2 | 6.6<br>5.9     | 10.3<br>9.7 | 2.54 | 15.0<br>12.8 | 3.30<br>2.79       | 3.0                        | 3.8<br>3.5 | 3.0<br>2.7 | 2.6<br>2.2 |

#### Notes

- Lead shoulder designs may vary.
- Dimension includes excess dambar.

| OUTLINE<br>VERSION | REFERENCES |                 |       |  | EUROPEAN<br>PROJECTION | ISSUE DATE           |
|--------------------|------------|-----------------|-------|--|------------------------|----------------------|
|                    | IEC        | JEDEC           | JEITA |  |                        |                      |
| SOT78              |            | 3-lead TO-220AB | SC-46 |  |                        | 08-04-23<br>08-06-13 |

Fig. 12. Package outline TO-220AB (SOT78)

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|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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## NXP Semiconductors

## BT234-600E

4Q Triac

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Date of release: 23 September 2013

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